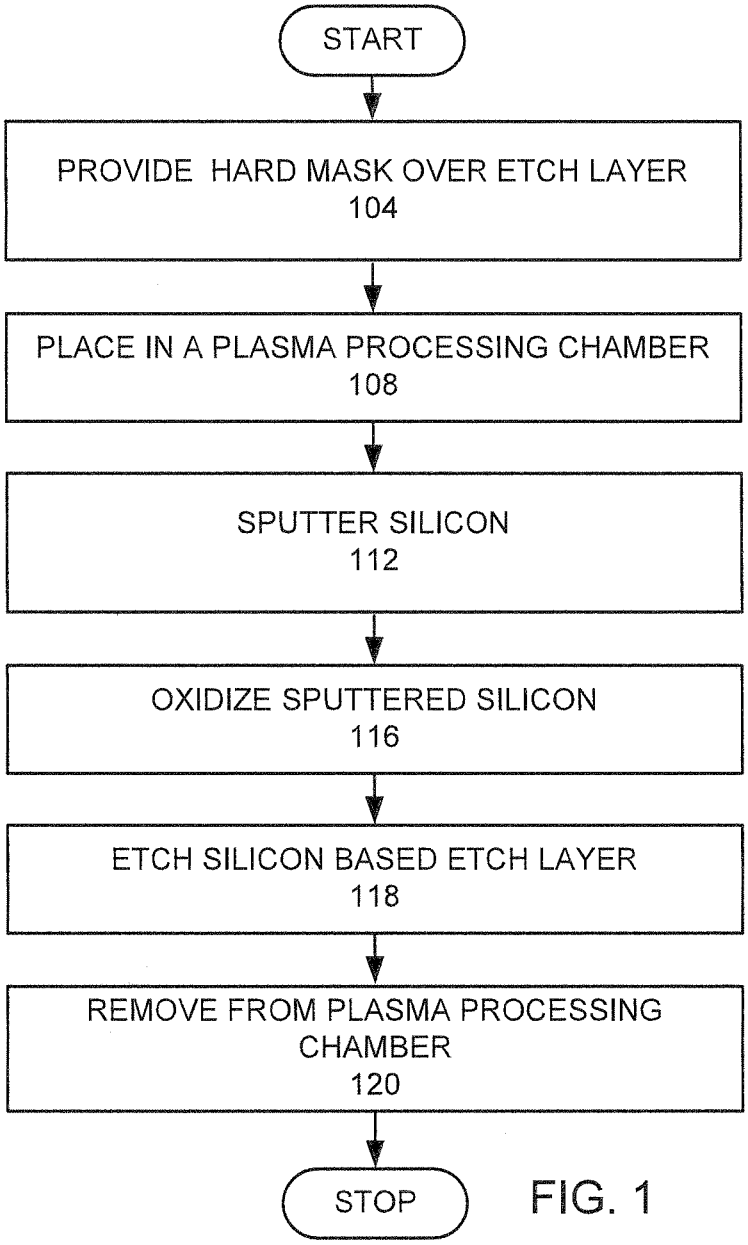

START
PROVIDE HARD MASK OVER ETCH LAYER
104
PLACE IN A PLASMA PROCESSING CHAMBER
108
SPUTTER SILICON
112
OXIDIZE SPUTTERED SILICON
116
ETCH SILICON BASED ETCH LAYER
118
REMOVE FROM PLASMA PROCESSING CHAMBER
120
STOP

FIG. 1

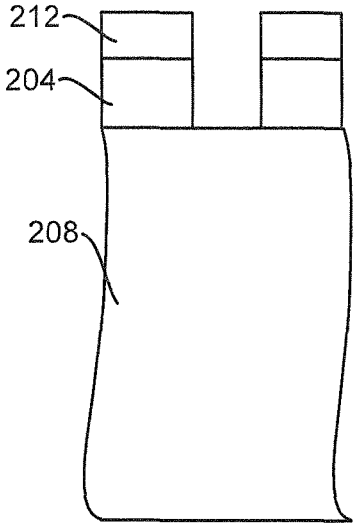


FIG. 2A

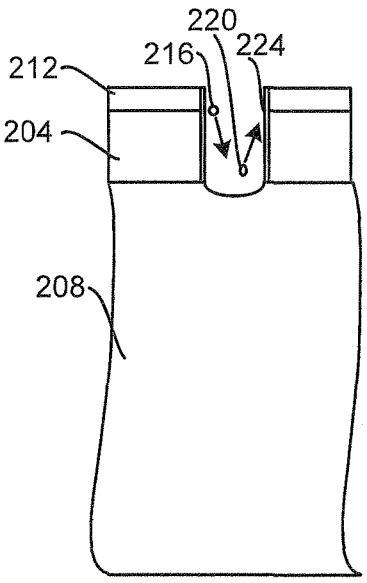


FIG. 2B

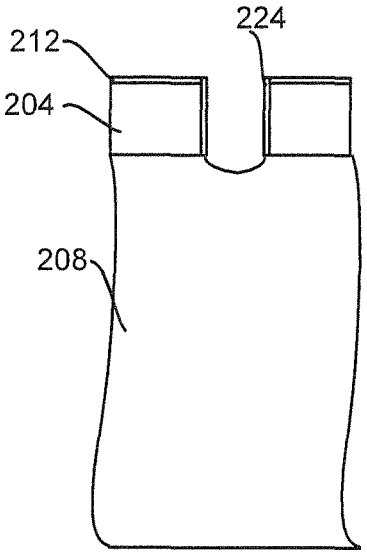


FIG. 2C

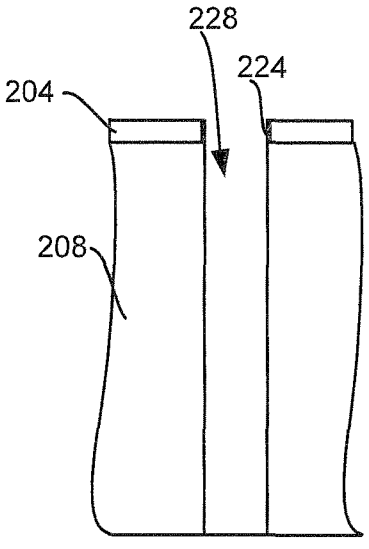


FIG. 2D

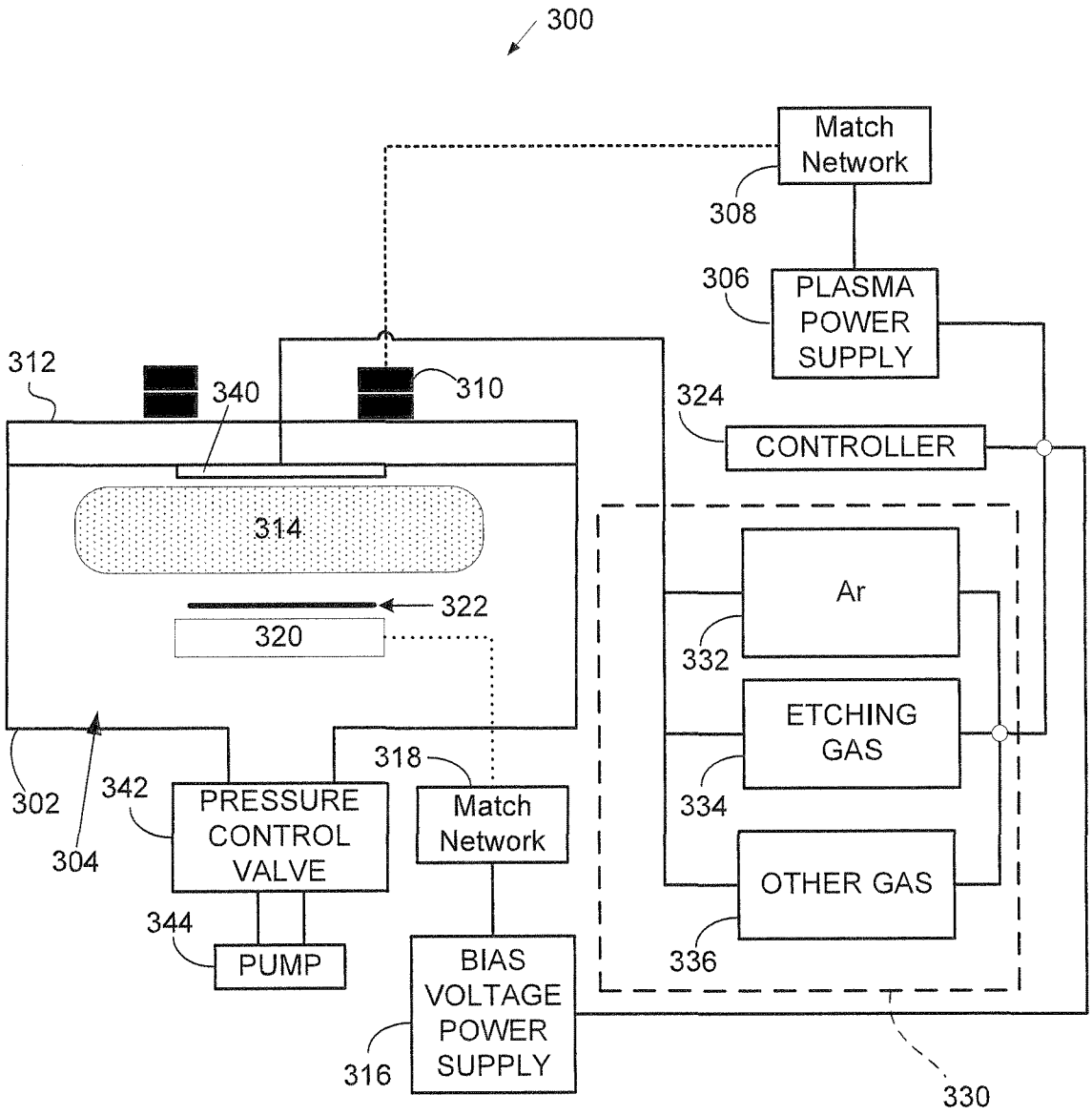

300
Match Network
308
306
PLASMA POWER SUPPLY
312
340
310
324
CONTROLLER
314
322
320
Ar
332
ETCHING GAS
334
OTHER GAS
336
318
302
342
304
PRESSURE CONTROL VALVE
Match Network
344
PUMP
BIAS VOLTAGE POWER SUPPLY
316
330

FIG. 3

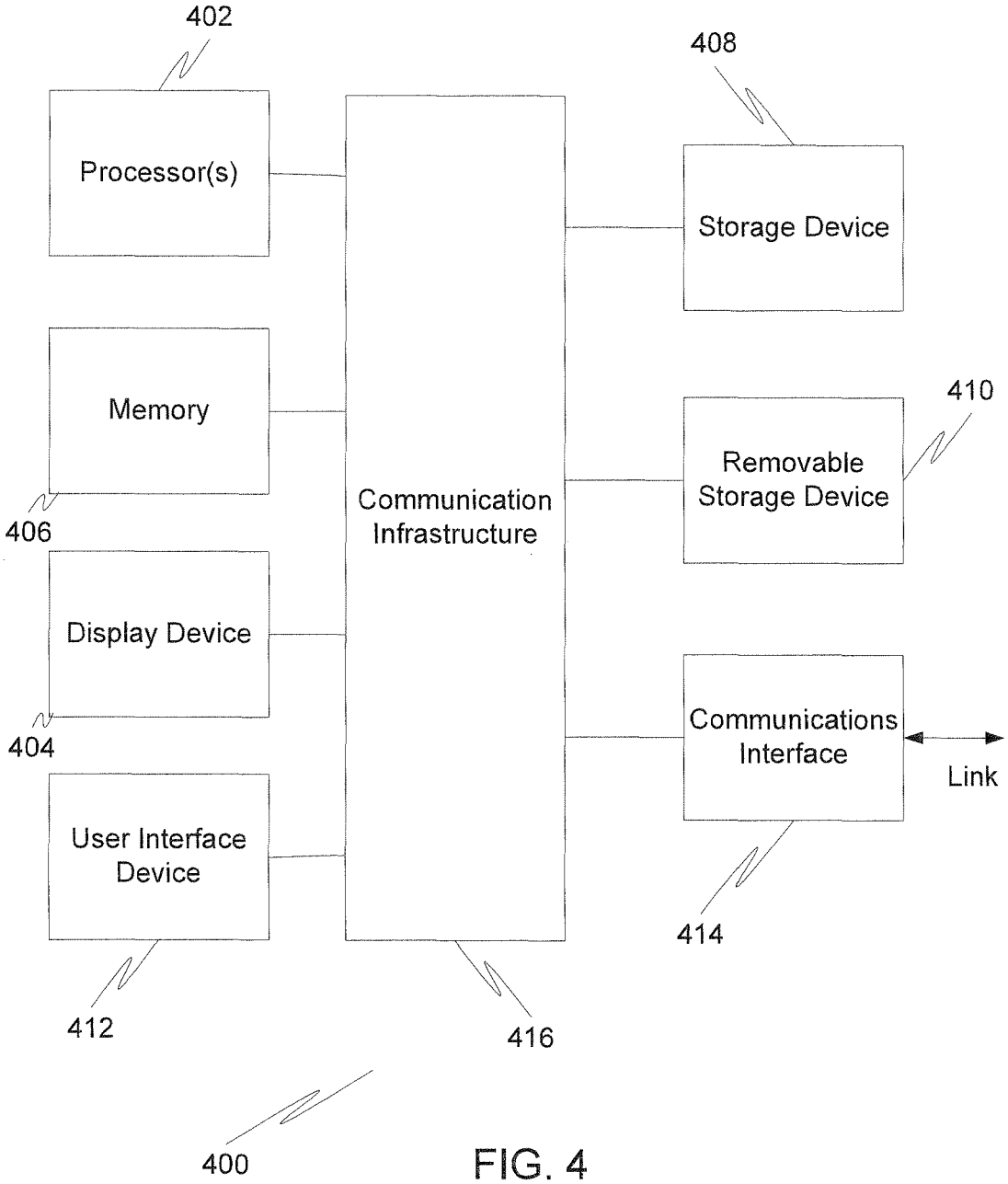

402
Processor(s)
408
Storage Device
Memory
406
Communication Infrastructure
410
Removable Storage Device
Display Device
404
Communications Interface
Link
User Interface Device
414
412
416
400

FIG. 4

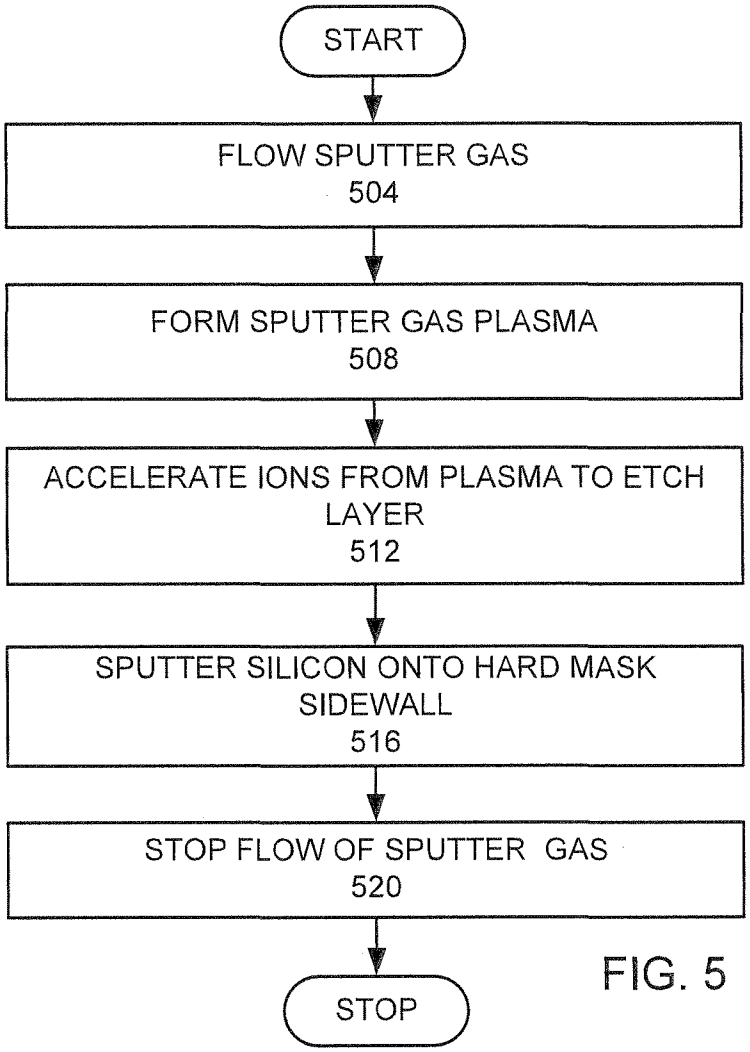

START
FLOW SPUTTER GAS
504
FORM SPUTTER GAS PLASMA
508
ACCELERATE IONS FROM PLASMA TO ETCH LAYER
512
SPUTTER SILICON ONTO HARD MASK SIDEWALL
516
STOP FLOW OF SPUTTER GAS
520
STOP

FIG. 5

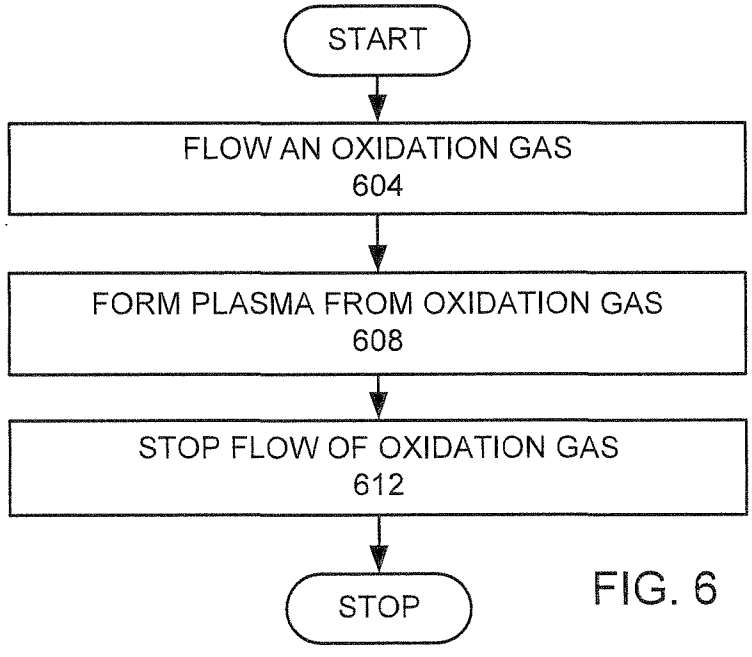

START
FLOW AN OXIDATION GAS
604
FORM PLASMA FROM OXIDATION GAS
608
STOP FLOW OF OXIDATION GAS
612
STOP

FIG. 6

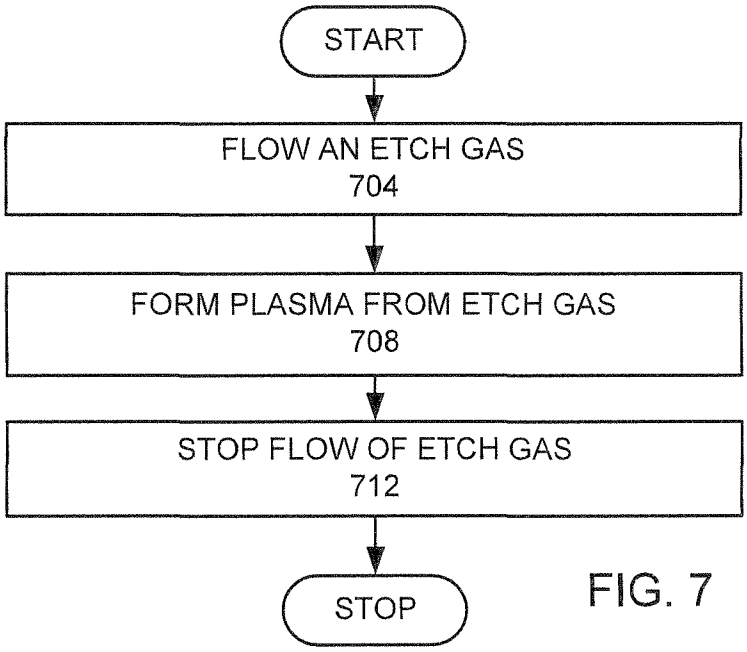

START
FLOW AN ETCH GAS
704
FORM PLASMA FROM ETCH GAS
708
STOP FLOW OF ETCH GAS
712
STOP

FIG. 7